

## Amendments to the Claims

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

### Listing of Claims

1. (currently amended) A fabrication method of a semiconductor integrated circuit device, comprising the steps of:
  - (a) forming an insulating film over a semiconductor ~~wafersubstrate~~;
  - (b) after the step (a), inserting the semiconductor ~~wafer substrate~~ into a thermal chemical vapor deposition chamber of a first film forming apparatus;
  - (c) heating the inside of the ~~deposition~~ chamber; and
  - (d) after the step (c), forming a silicon film added with a conductive impurity over the insulating film by a chemical ~~film-forming vapor deposition~~ method,said step (c) comprising the sub-steps of:
  - (c1) heating the inside of the ~~deposition~~ chamber while keeping the inside of the ~~deposition~~ chamber at atmospheric pressure; and
  - (c2) after the sub-step (c1), heating the inside of the ~~deposition~~ chamber while adjusting the pressure inside of the ~~deposition~~ chamber to vacuum or not greater than atmospheric pressure,wherein a time required for the sub-step (c1) is longer than a time required for the sub-step (c2).
2. (currently amended) A fabrication method of a semiconductor integrated circuit device, comprising the steps of:
  - (a) forming an insulating film over a semiconductor ~~wafersubstrate~~;

(b) after the step (a), inserting the semiconductor wafer substrate into a thermal chemical vapor deposition chamber of a first film forming apparatus;

(c) heating the inside of the ~~deposition~~ chamber; and

(d) after the step (c), forming a silicon film added with a conductive impurity over the insulating film by a chemical ~~film forming~~ vapor deposition method,

said step (c) comprising the sub-steps of:

(c1) heating the inside of the ~~deposition~~ chamber while keeping the inside of the ~~deposition~~ chamber at atmospheric pressure; and

(c2) after the sub-step (c1), heating the inside of the ~~deposition~~ chamber while adjusting a pressure inside of the ~~deposition~~ chamber to vacuum or not greater than atmospheric pressure,

wherein a time required for the sub-step (c1) is 0.1 time or greater but not greater than 13 times as long as a time required for the sub-step (c2).

3. - 13. (cancelled)

14. (new) A fabrication method of a semiconductor integrated circuit device, comprising the steps of:

(a) forming an insulating film over a semiconductor wafer;

(b) after the step (a), inserting the semiconductor wafer into a thermal chemical vapor deposition chamber of a first film forming apparatus;

(c) heating the semiconductor wafer while keeping the inside of the chamber at a first pressure;

(d) after the step (c), reducing a pressure in the chamber to be not greater than a second pressure, while heating the semiconductor wafer; and

(e) forming a silicon film added with a conductive impurity over the insulating film by a chemical vapor deposition method while keeping a pressure in the chamber at vacuum or a third pressure not greater than atmospheric pressure,

wherein in the step (d), pressure is reduced so that the second pressure becomes lower than the third pressure,

wherein in the step (c), the semiconductor wafer is heated to bring a temperature thereof close to the first temperature while maintaining the first pressure to be higher than the third pressure, and

wherein a time required for the step (c) is longer than that required for the step (d).

15. (new) A fabrication method of a semiconductor integrated circuit device, comprising the steps of:

(a) forming an insulating film over a semiconductor wafer;

(b) after the step (a), inserting the semiconductor wafer into a thermal chemical vapor deposition chamber of a first film forming apparatus;

(c) heating the semiconductor wafer while keeping the inside of the chamber at a first pressure;

(d) after the step (c), reducing a pressure in the chamber to be not greater than a second pressure, while heating the semiconductor wafer; and

(e) forming a silicon film added with a conductive impurity over the insulating film by a chemical vapor deposition method while keeping a pressure in the chamber at vacuum or a third pressure not greater than atmospheric pressure,

wherein in the step (d), pressure is reduced so that the second pressure becomes lower than the third pressure,

wherein in the step (c), the semiconductor wafer is heated to bring a temperature thereof close to the first temperature while maintaining the first pressure to be higher than the third pressure, and

wherein the time required for the step (c) is 0.1 time or greater but not greater than 13 times as long as the time required for the step (d).